

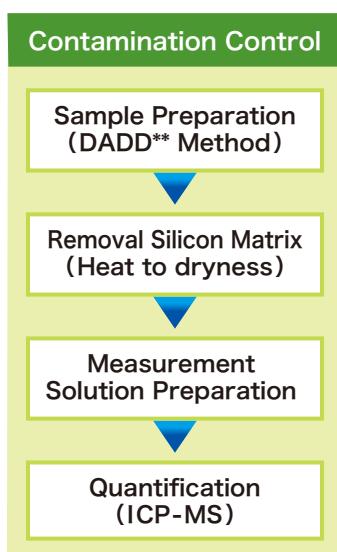
# Wafer Surface Contamination

# Wafer表面之超高感度汙染評估

## 使用DADD-ICP-MS方法進行微量元素定量分析

# 300mm Wafer 表面之微量金屬分析

使用先進的汙染控制技術與高感度ICP-MS方法，可以在  $E+4 \sim 6 \text{ atoms/cm}^2$  檢出定量下限之規格，評估 Silicon Wafer 表面之微量金屬汙染。



## Method Detection Limits (MDL) \*\*\*

### Method Quantification Limits (MQL) \*\*\*

\* SEMI M85-1114 : GUIDE FOR THE MEASUREMENT OF TRACE METAL CONTAMINATION ON SILICON WAFER SURFACE BY ICP-MS

### \*\* DADD : Direct Acid Droplet Decomposition

\*\*\* MDL : Method Detection Limits, MQL : Method Quantification Limits, Obtained by  $k \times SD/s$

*K (MDL) : a coefficient ( $k=3$  has been used in JISKO133) SD : the standard deviation of the intensity of the method blank solutions*

$k$  (MDE) : a coefficient ( $k=5$  has been used in JISK0133)    $SD$  : the standard deviation of the intercept  
 $k$  (MQL) : a coefficient ( $k=10$  has been used in JISK0133)    $s$  : the slope of the calibration curve

超微量化學汙染評估

從既有的經驗與知識，獨自設計之無化學汙染無塵室，可評估超微量表面分子狀汙染物質。  
(SMCs : Surface Molecular Contaminants)

< 無金屬汙染實驗室 >

< 無有機物汙染實驗室 >

< 無離子汙染實驗室 >



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